

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

Claims 1-16 (Canceled)

17. (Currently Amended) Light emitting semiconductor body for use in an LED housing,
said semiconductor body being provided with a layer comprising a wavelength-
converting casting composition; and
said casting composition comprising luminous substance particles;
said luminous substance particles comprising luminous substance pigments
selected from the group consisting of garnets doped with rare earths; thiogallates doped
with rare earths; aluminates doped with rare earths; and orthosilicates doped with rare
earths; and
said luminous substance pigments having grain sizes $\leq 20 \mu\text{m}$ and ~~a mean grain~~
~~diameter~~ d_{50} a median diameter $\leq 5 \mu\text{m}$, wherein 50% of the pigments have a grain
diameter greater than said median diameter and 50% of the pigments have a grain
diameter less than said median diameter.
18. Canceled.
19. Canceled.

20. (Currently Amended) Semiconductor body according to claim 17, wherein the median diameter ~~mean grain diameter~~ d_{50} of said luminous substance pigments is between 1 and 2 micrometers.
21. (Previously Presented) Semiconductor body according to claim 17, wherein said luminous substance pigments contain Ce-doped garnet material.
22. (Previously Presented) Semiconductor body according to claim 17, wherein said luminous substance pigments contain YAG:Ce material.
23. (Previously Presented) Semiconductor body according to claim 17, wherein the iron content in the casting composition is ≤ 20 ppm.
24. (Previously Presented) Semiconductor body according to claim 17, wherein the luminous substance pigments are provided with a silicone coating.
25. (Previously Presented) Semiconductor body according to claim 17, wherein said luminous substance pigments convert radiation from the ultraviolet, blue or green spectral range into light with a relatively longer wavelength.
26. (Previously Presented) Semiconductor body according to claim 17, wherein said layer containing light-scattering particles.
27. (Previously Presented) Semiconductor body according to claim 17, wherein said semiconductor body is adapted to emit radiation in a blue spectral range having a maximum luminescence intensity at a wavelength between 420 nm and 460 nm.
28. (Currently Amended) Light emitting semiconductor body for use in an LED housing,

said semiconductor body being provided with a layer comprising a wavelength-converting casting composition; and

said casting composition comprising luminous substance particles;

said luminous substance particles comprising luminous substance pigments from Ce-doped phosphors; and

said luminous substance pigments having grain sizes $\leq 20 \mu\text{m}$ and ~~a mean grain diameter~~ a median diameter $\leq 5 \mu\text{m}$, wherein 50% of the pigments have a grain diameter greater than said median diameter and 50% of the pigments have a grain diameter less than said median diameter.

29. Canceled.

30. Canceled.

31. (Currently Amended) Semiconductor body according to claim 28, wherein the median diameter ~~mean grain diameter~~ d_{50} of said luminous substance pigments is between 1 and 2 micrometers.

32. (Previously Presented) Semiconductor body according to claim 28, wherein the iron content in the casting composition is ≤ 20 ppm.

33. (Previously Presented) Semiconductor body according to claim 28, wherein the luminous substance pigments are provided with a silicone coating.

34. (Previously Presented) Semiconductor body according to claim 28, wherein said luminous substance pigments convert radiation from the ultraviolet, blue or green spectral range into light with a relatively longer wavelength.

35. (Previously Presented) Semiconductor body according to claim 28, wherein said layer containing light-scattering particles.
36. (Previously Presented) Semiconductor body according to claim 28, wherein said semiconductor body is adapted to emit radiation in a blue spectral range having a maximum luminescence intensity at a wavelength between 420 nm and 460 nm.
37. (Previously Presented) Semiconductor body according to claim 17, wherein the casting composition further comprises a transparent resin.
38. (Previously Presented) Semiconductor body according to claim 37, wherein the transparent resin is an epoxy resin.
39. (Previously Presented) Semiconductor body according to claim 28, wherein the casting composition further comprises a transparent resin.
40. (Previously Presented) Semiconductor body according to claim 39, wherein the transparent resin is an epoxy resin.